



APPENDIX

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IN THE CLAIMS:

Please cancel claims 18 and 19 without prejudice or disclaimer.

Please amend claims 1, 14 and 15 as follows:

1. (Amended) A semiconductor device comprising:

a substrate;

a source/drain diffused layer formed in the substrate for a transistor; and

a dummy diffused layer formed in the substrate,

wherein the source/drain diffused layer has its surface silicided, and

wherein the dummy diffused layer has its surface covered with an anti-silicidation

film at least partially, on which no gate electrode is provided.

112, 1st (13) is gate--
see fig. 4B

14. (Amended) A semiconductor device comprising:

a substrate;

a source/drain diffused layer formed in the substrate for a transistor; and

a dummy diffused layer formed in the substrate,

wherein the source/drain diffused layer has its surface silicided, and

wherein the dummy diffused layer has its surface covered with an anti-silicidation

film at least partially, and

[The device of claim 1,] wherein the dummy diffused layer is located between [a] an
analog circuit block and [another] a digital circuit block.

15. (Amended) A semiconductor device comprising:

a substrate;

a source/drain diffused layer formed in the substrate for a transistor; and

a dummy diffused layer formed in the substrate,

wherein the source/drain diffused layer has its surface silicided, and

wherein the dummy diffused layer has its surface covered with an anti-silicidation
film at least partially, and

[The device of claim 1,] wherein the dummy diffused layer is not electrically coupled to
another component via an interconnect.